

#4 Preliminary
8-12-95

Docket: 0756-1299

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional PATENT application of)
 Hongyong ZHANG et al.)
 Based on Serial No. 08/248,220) Art Unit: 2508
 Filed: June 5, 1995) Examiner: S. Loke
 For: SEMICONDUCTOR DEVICE AND)
 FABRICATION METHOD OF THE)
 SAME) June 5, 1995

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents and Trademarks
 Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIMS

Add new claims 14-25 as follows:

--14. A method for fabricating a semiconductor device, comprising the steps of:

forming a silicon film having an amorphous on a substrate;
 preparing a metal element which promotes crystallization before
 or after formation of the silicon film, to introduce the metal element into an
 introducing region of the silicon film; and
 crystallizing the silicon film,
 wherein the silicon film is crystal-grown from the introducing

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